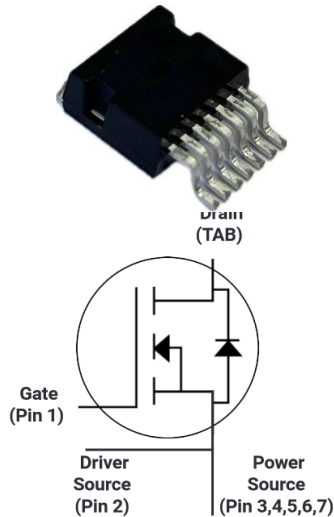


Silicon Carbide Power MOSFET (N-Channel Enhancement)

V_{DS}	1200V
I_D (25°C)	29A
$R_{DS(on)}$	70mΩ



Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free, RoHS compliant

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- **Package:** TO-263-7L
- **Terminals:** Tin plated leads
- **Polarity:** As marked

■Maximum Ratings ($T_c=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code			D212080B7YG3		
Drain source voltage @ $T_j=25^\circ\text{C}$	$V_{DS,max}$	V	1200	$V_{GS}=0V$, $I_D=100\mu A$	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,max}$	V	-8/+22	Absolute maximum values (AC f >1Hz, duty cycle < 1%)	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,op}$	V	-5/+18	Recommended operational values	
Continuous drain current @ $T_c=25^\circ\text{C}$	I_D	A	29	$V_{GS}=18V$, $T_c=25^\circ\text{C}$	Fig.17
Continuous drain current @ $T_c=100^\circ\text{C}$			20	$V_{GS}=18V$, $T_c=100^\circ\text{C}$	
Pulsed drain current	$I_{D(pulsed)}$	A	85	Pulse width t_p limited by $T_{j,max}$	Fig.22
Avalanche energy,Single pulse	E_{AS}	mJ	402	$V_{DD}=75V$, $L=30mH$	
Power Dissipation	P_{TOT}	W	116	$T_c=25^\circ\text{C}$, $T_j = 175^\circ\text{C}$	Fig.16
Power Dissipation			58	$T_c=100^\circ\text{C}$, $T_j = 175^\circ\text{C}$	
Operating junction and Storage temperature range	T_j, T_{stg}	$^\circ\text{C}$	-55 to +175		
Soldering temperature	T_L	$^\circ\text{C}$	260	1.6mm (0.063") from case for 10s	
Mounting torque	T_M	Nm	0.6	M3 screw Maximum of mounting process: 3	



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■Static Electrical Characteristics (Tc=25℃ unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	$V_{GS(th)}$	V	2.0	3.0	4.0	$V_{DS}=V_{GS}$, $I_D=6mA$	Fig.4, 11
				2.4		$V_{DS}=V_{GS}$, $I_D=6mA$, $T_j=175^\circ C$	
Drain source breakdown voltage	$V_{(BR)DSS}$	V	1200			$V_{GS}=0V$, $I_D=100\mu A$	
Drain source leakage current	I_{DSS}	μA		10	100	$V_{DS}=1200V$, $V_{GS}=0V$	
Gate source leakage current	I_{GSS}	nA		10	100	$V_{GS}=18V$, $V_{DS}=0V$	
Current drain source on-state resistance	$R_{DS\ ON}$	m Ω		80		$V_{GS}=15V$, $I_D=15A$	Fig.5, 6, 7
				70	92	$V_{GS}=18V$, $I_D=15A$	
				130		$V_{GS}=15V$, $I_D=15A$, $T_j=175^\circ C$	
				125		$V_{GS}=18V$, $I_D=15A$, $T_j=175^\circ C$	
Transconductance	g_f	S		10.2		$V_{DS}=20V$, $I_D=15A$	Fig.4
				10		$V_{DS}=20V$, $I_D=15A$, $T_j=175^\circ C$	

■Dynamic Electrical Characteristics (Tc=25℃ unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	C_{iss}	pF		1665		$V_{DS}=800V$, $V_{GS}=0V$, $T_j=25^\circ C$, $f=1\text{ MHz}$, $V_{AC}=25mV$	Fig.13, 14
Output capacitance	C_{oss}			71			
Reverse capacitance	C_{rss}			3.2			
Coss stored energy	E_{oss}	μJ		27.5			Fig.15
Gate source charge	Q_{gs}	nC		15.7		$V_{DS}=800V$, $V_{GS}=-5/18V$, $I_D=15A$	Fig.12
Gate drain charge	Q_{gd}			39.4			
Gate charge	Q_g			64.2			
Internal gate resistance	R_g	Ω		1.2		$f=1MHz$	

■Switching Characteristics (Tc=25℃ unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on delay time	$t_{d(on)}$	ns		7		$V_{DD}=800V$, $V_{GS}=-5/+18V$, $I_D=15A$, $R_g=2.4\Omega$, $L=200\mu H$	Fig.21
Rise time	t_r			10			
Turn off delay time	$t_{d(off)}$	ns		14.5			
Fall time	t_f			12.2			



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Turn on switching energy	E_{on}	uJ		154		$V_{DD}=800V, V_{GS}=-5/+18V, I_D=15A,$ $R_g=2.4\Omega, L=200\mu H$	Fig.19, 20
Turn off switching energy	E_{off}			45			

■Body diode characteristics (T_c=25℃ unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	V_{SD}	V		4.2		$V_{GS}=-5V, I_{SD}=7.5A$	Fig.8
				3.5		$V_{GS}=0V, I_{SD}=7.5A, T_j=175^\circ C$	Fig.9
Continuous diode forward current	I_S	A		19		$V_{GS}=-5V, T_c=25^\circ C$	
Reverse recovery time	t_{rr}	nS		14.5		$V_R=800V, V_{GS}=-5V, I_D=15A,$ $di/dt=2000A/\mu S$	
Reverse recovery charge	Q_{rr}	nC		101			
Peak reverse recovery current	I_{rrm}	A		11.5			

■Thermal Characteristics (T_a=25℃ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Typ.
Thermal resistance	$R_{\theta J-C}$	°C/W	1.29

■Typical Characteristics

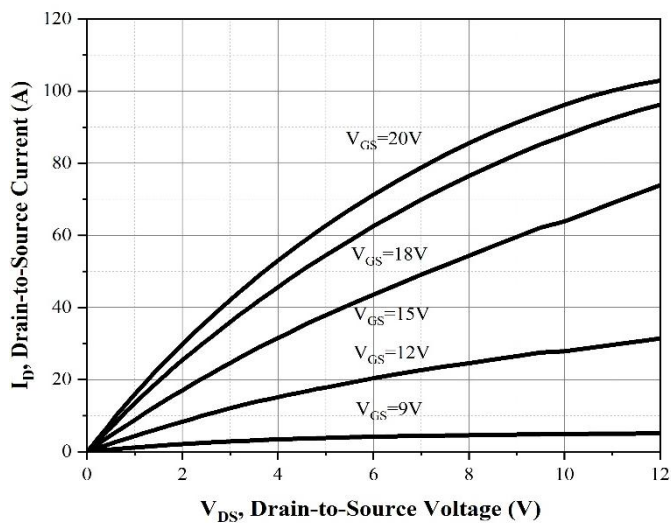


Figure 1. Output Characteristics T_j = -55℃

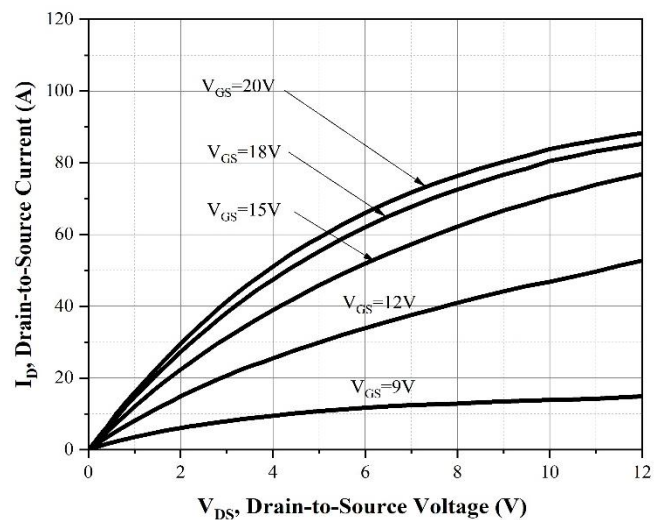


Figure2. Output Characteristics T_j = 25℃

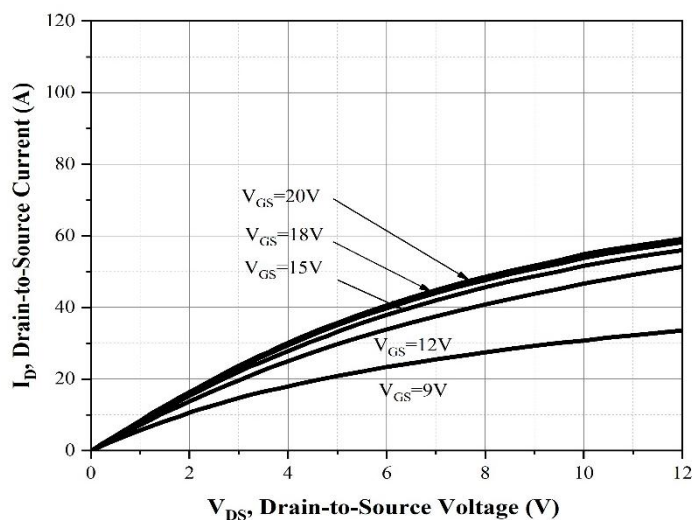


Figure 3. Output Characteristics $T_j = 175^\circ\text{C}$

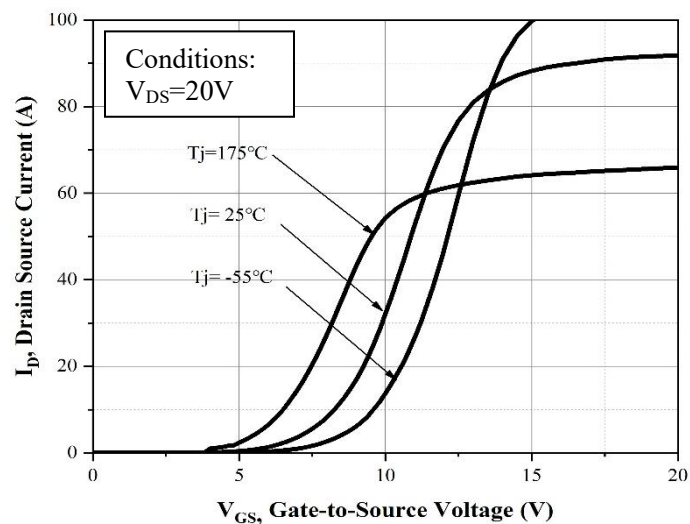


Figure 4. Transfer Characteristics for Various Junction Temperature

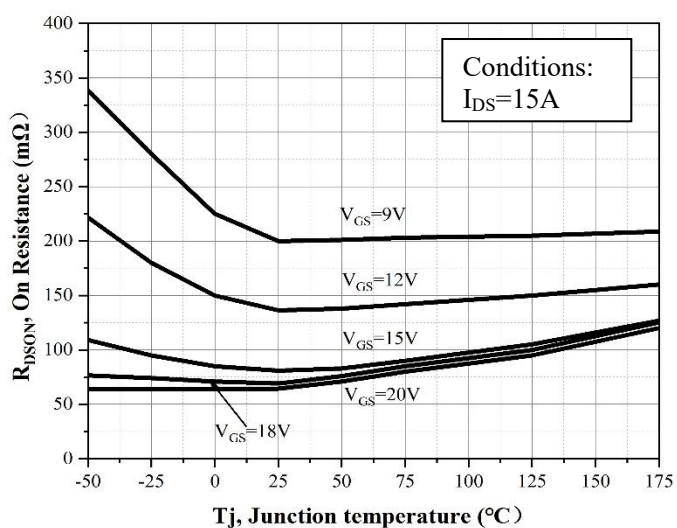


Figure 5. On-resistance vs. Temperature for Various Gate Voltage

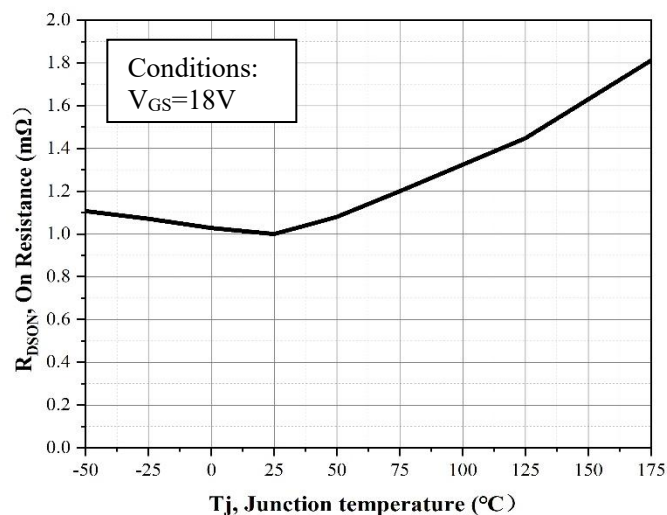


Figure 6. Normalized on-resistance vs. Temperature

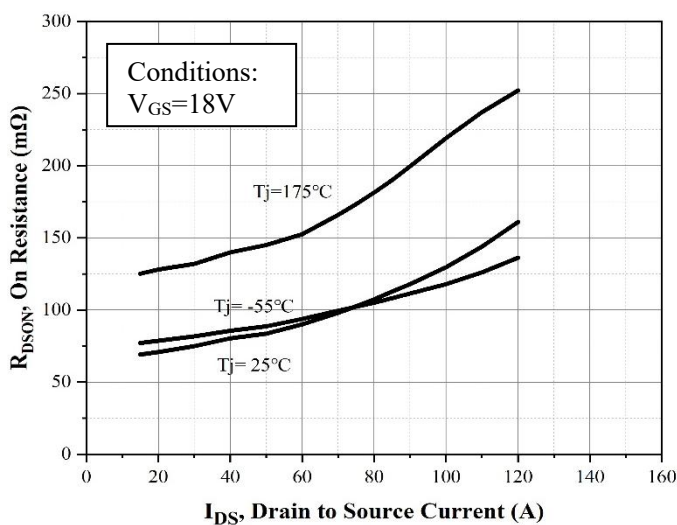


Figure 7. On-resistance vs. Drain Current

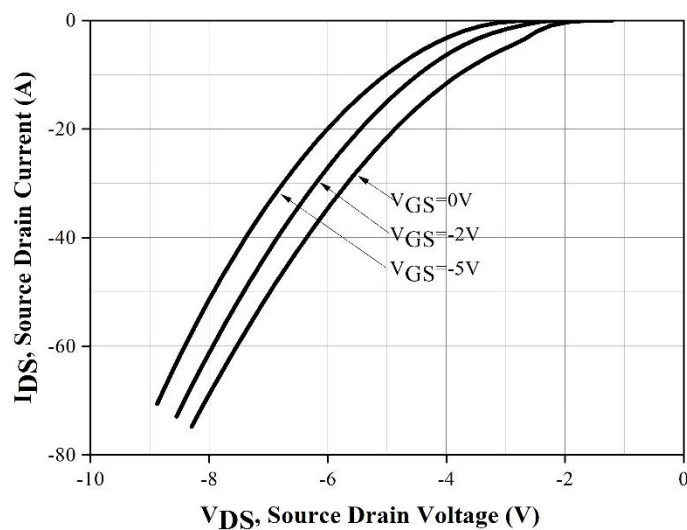


Figure 8. Body Diode Characteristic at $T_j = 25^\circ\text{C}$

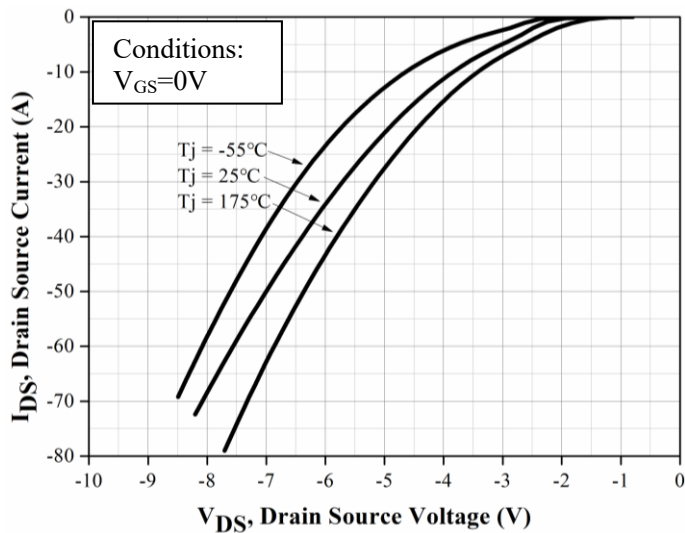


Figure 9. Body Diode Characteristic

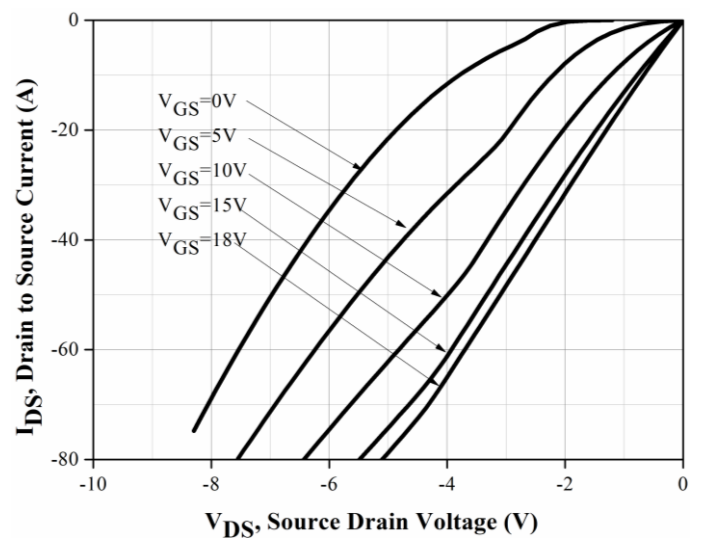


Figure 10. 3rd quadrant Characteristic at T_j= 25 °C

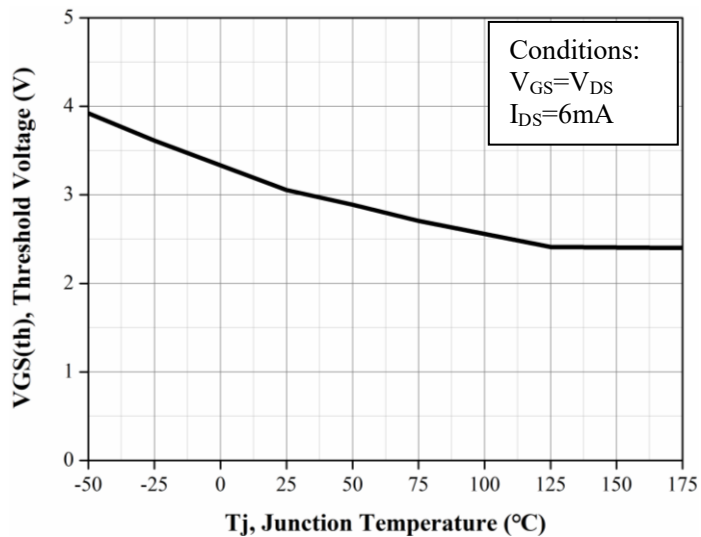


Figure 11. Threshold Voltage vs. Temperature

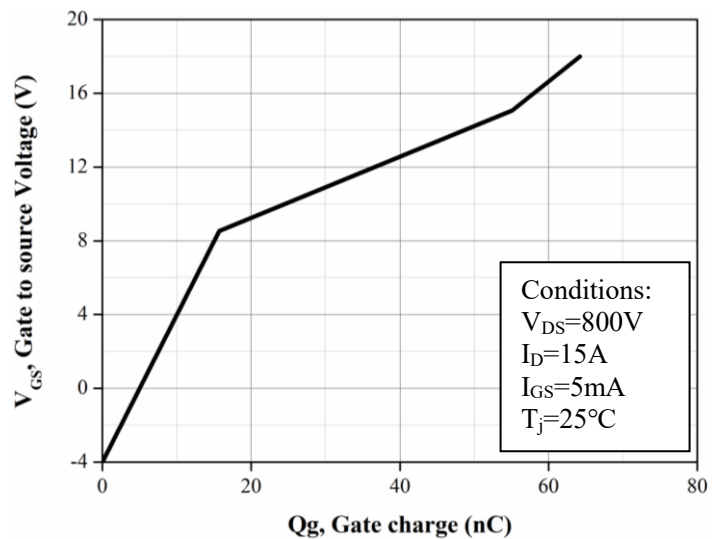


Figure 12. Gate Charge Characteristic

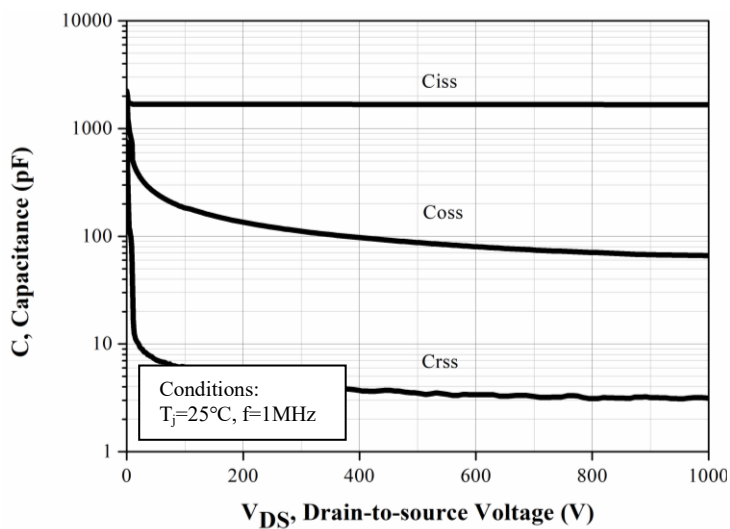


Figure 13. Capacitances vs. Drain Source Voltage (0-1000V)

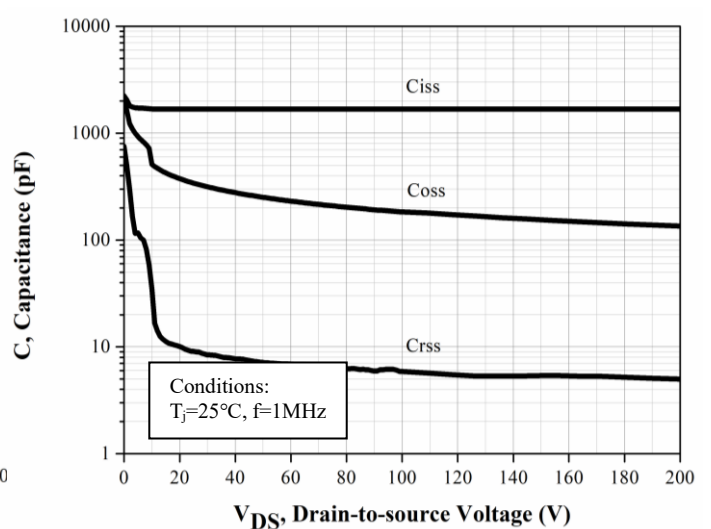


Figure 14. Capacitances vs. Drain Source Voltage (0-200V)



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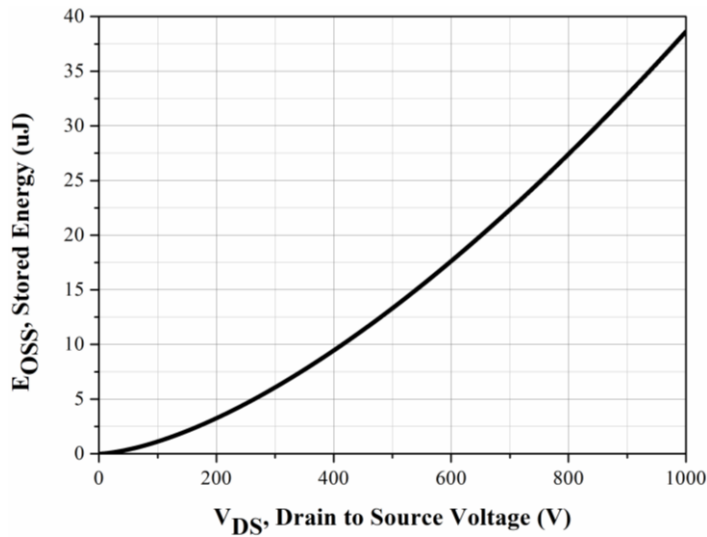


Figure 15. Output Capacitor Stored Energy

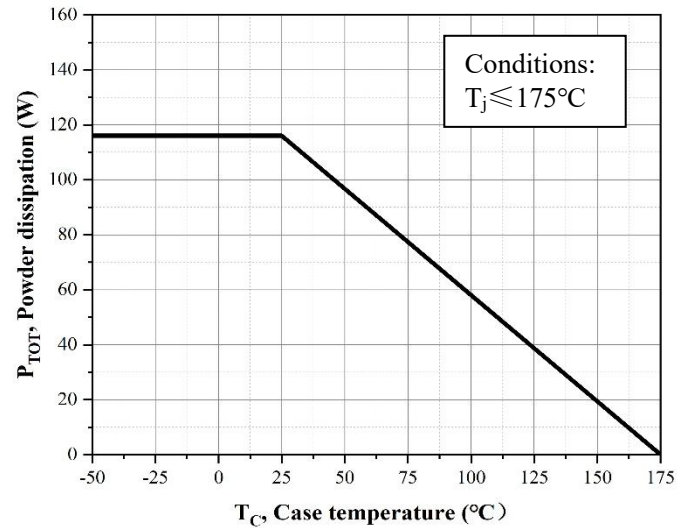


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

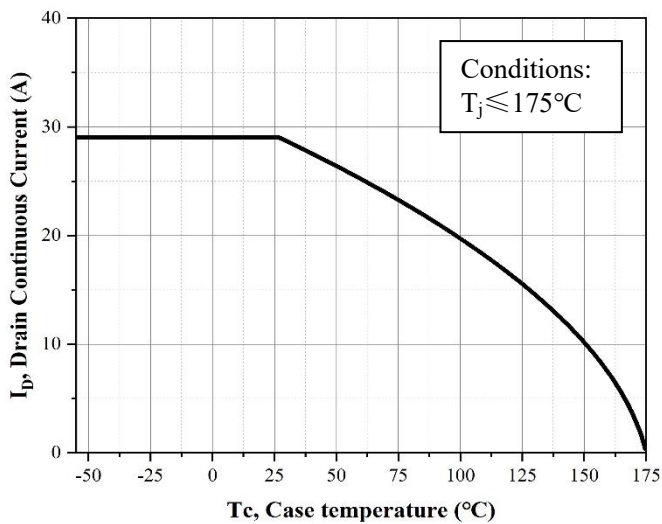


Figure 17. Continuous Drain Current Derating vs. Case Temperature

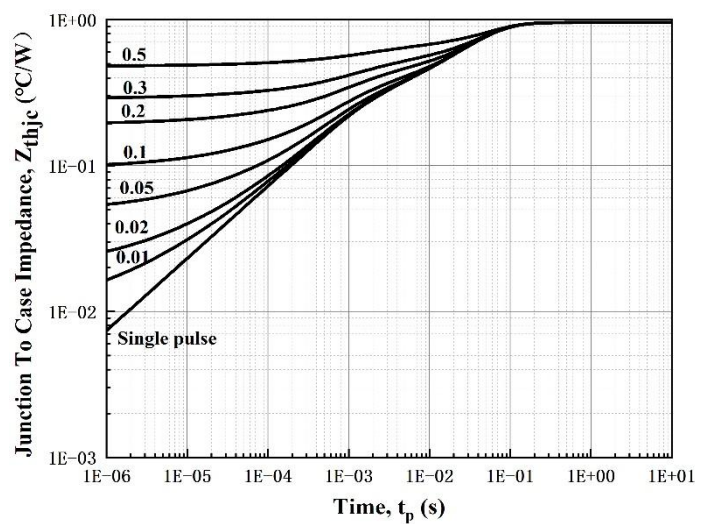


Figure 18. Transient Thermal Impedance (Junction - Case)

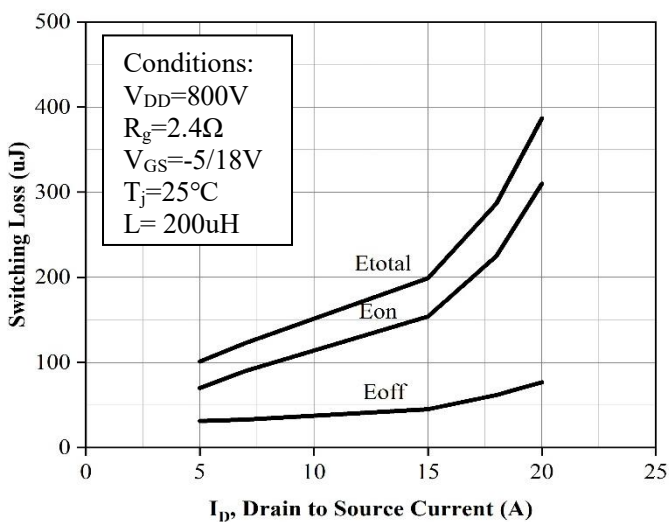


Figure 19. Clamped Inductive Switching Energy vs. Drain Current

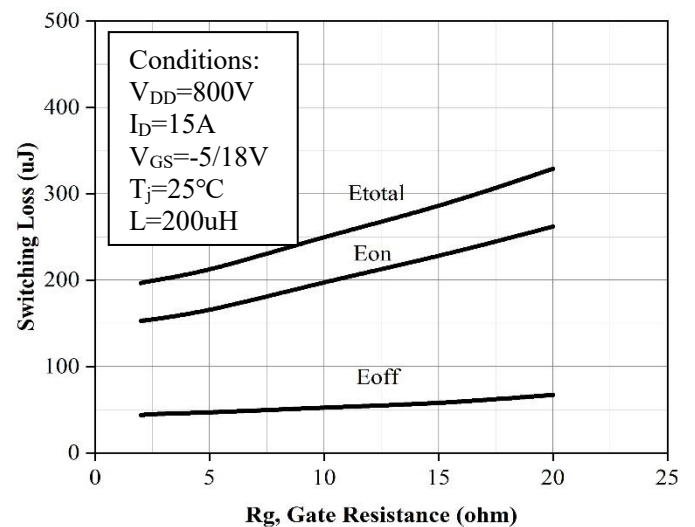


Figure 20. Clamped Inductive Switching Energy vs. R_g

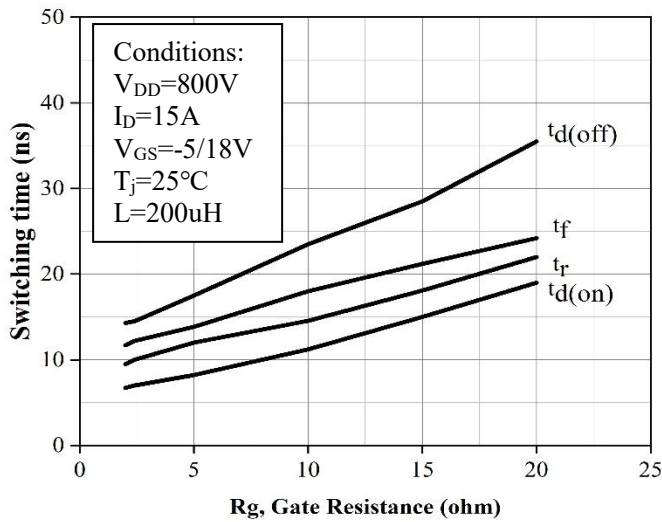


Figure 21. Switching Times vs. R_g

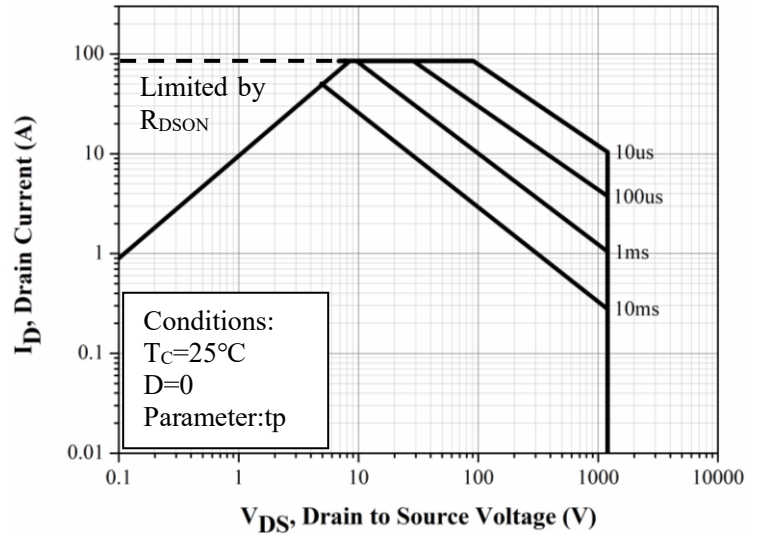


Figure 22. Safe Operating Area

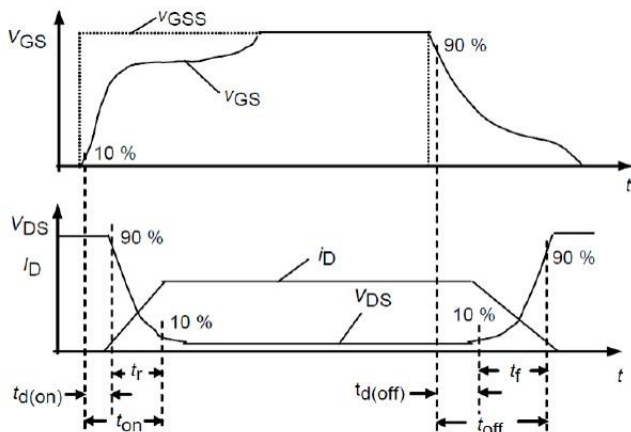


Figure 23. Switching Times Definition

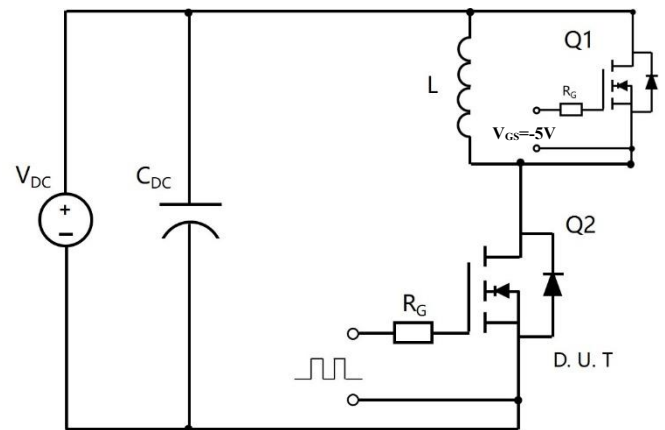
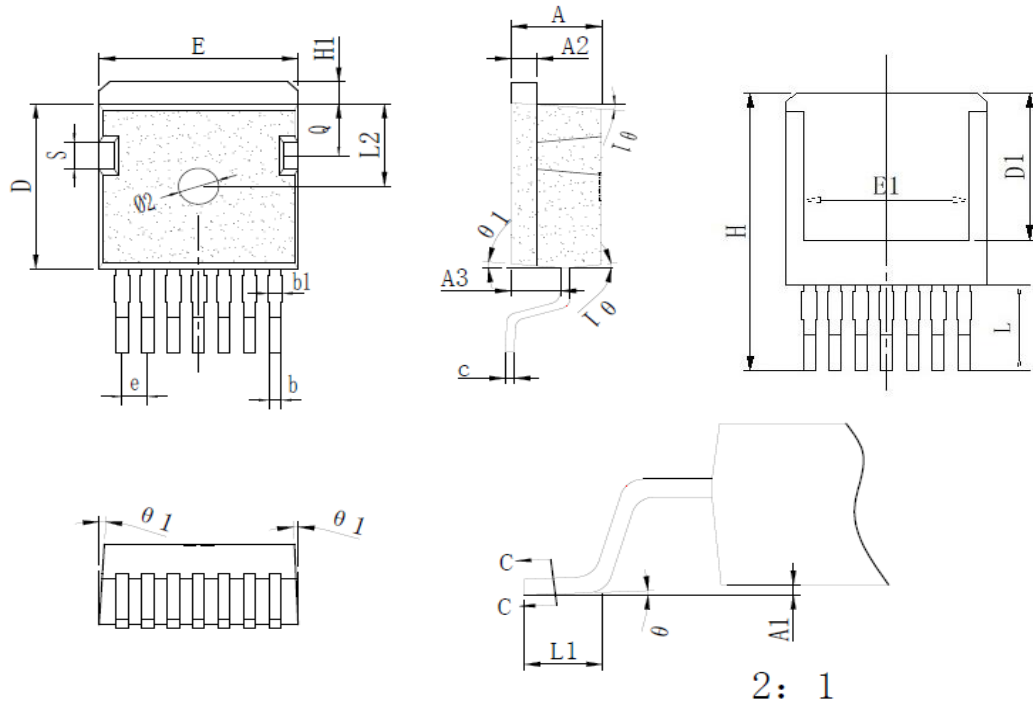


Figure 24. Clamped Inductive Switching Waveform Test Circuit



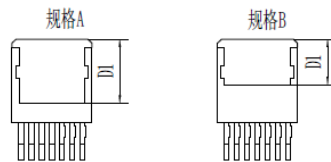
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■Outline Dimensions



2: 1

*为关键管控尺寸



SYMBOL	mm		
	MIN	NOM	MAX
*A	4.30	4.40	4.50
*A1	0.00	0.10	0.20
*A2	1.22	1.27	1.32
*A3	2.30	2.40	2.50
*b	0.50	0.60	0.70
*b1	-	-	0.63
*c	0.45	0.50	0.55
*D	9.15	9.30	9.45
D1	规格A: 8.00REF		
	规格B: 5.70REF		
*E	10.12	10.16	10.20
E1	8.20	8.40	8.60
*e	1.25	1.27	1.29
*H	14.85	15.00	15.15
H1	1.10	1.20	1.30
*L	4.50	4.70	4.90
L1	1.70	2.00	2.30
L2	4.55	4.65	4.75
S	1.40	1.50	1.60
Q	2.80	2.90	3.00
*theta	0°	2.5°	8°
theta1	5°	7°	9°



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